

DAN222

Common Cathode Silicon Dual Switching Diode

This Common Cathode Silicon Epitaxial Planar Dual Diode is designed for use in ultra high speed switching applications. This device is housed in the SOT-416/SC-90 package which is designed for low power surface mount applications, where board space is at a premium.

Features

- Fast t_{rr}
- Low C_D
- Available in 8 mm Tape and Reel
- Pb-Free Package is Available

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	80	Vdc
Peak Reverse Voltage	V_{RM}	80	Vdc
Forward Current	I_F	100	mAdc
Peak Forward Current	I_{FM}	300	mAdc
Peak Forward Surge Current	$I_{FSM}(1)$	2.0	Adc

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

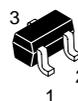
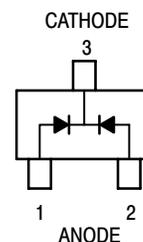
Rating	Symbol	Max	Unit
Power Dissipation	P_D	150	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$

1. $t = 1 \mu\text{S}$



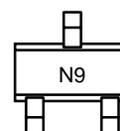
ON Semiconductor®

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SOT-416
CASE 463
STYLE 3

MARKING DIAGRAM



ORDERING INFORMATION

Device	Package	Shipping†
DAN222	SOT-416	3000/Tape & Reel
DAN222T1	SOT-416	3000/Tape & Reel
DAN222T1G	SOT-416 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

Characteristic	Symbol	Condition	Min	Max	Unit
Reverse Voltage Leakage Current	I_R	$V_R = 70\text{ V}$	—	0.1	μA dc
Forward Voltage	V_F	$I_F = 100\text{ mA}$	—	1.2	Vdc
Reverse Breakdown Voltage	V_R	$I_R = 100\ \mu\text{A}$	80	—	Vdc
Diode Capacitance	C_D	$V_R = 6.0\text{ V}, f = 1.0\text{ MHz}$	—	3.5	pF
Reverse Recovery Time	$t_{rr}(2)$	$I_F = 5.0\text{ mA}, V_R = 6.0\text{ V}, R_L = 100\ \Omega, I_{rr} = 0.1\ I_R$	—	4.0	ns

2. t_{rr} Test Circuit on following page.

TYPICAL ELECTRICAL CHARACTERISTICS

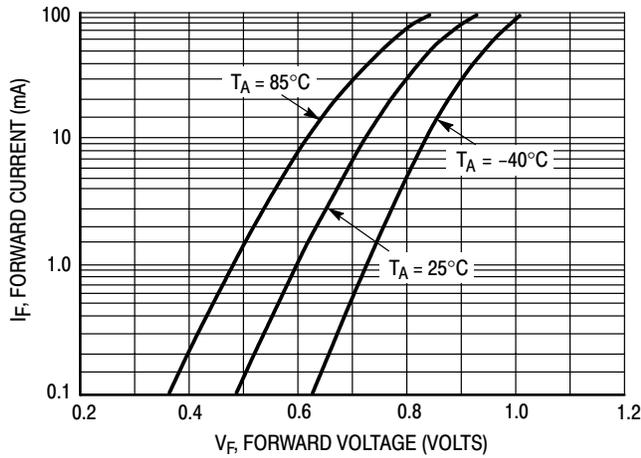


Figure 1. Forward Voltage

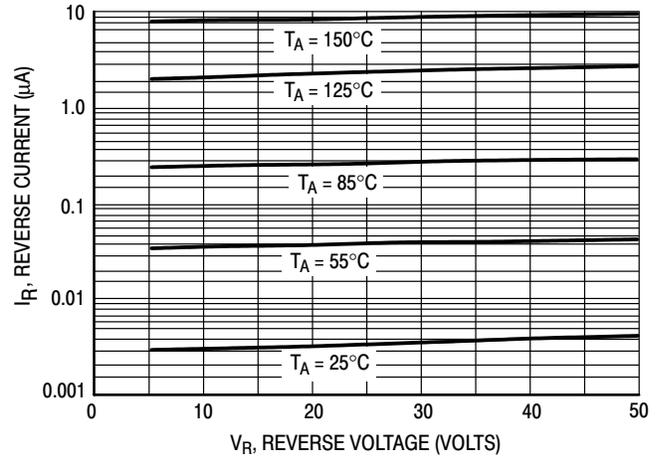


Figure 2. Reverse Current

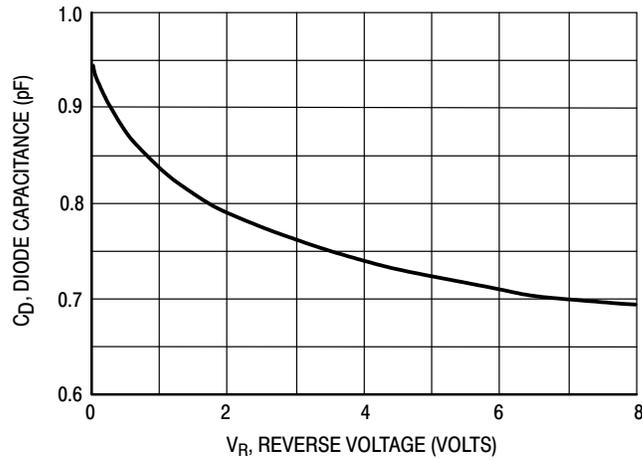
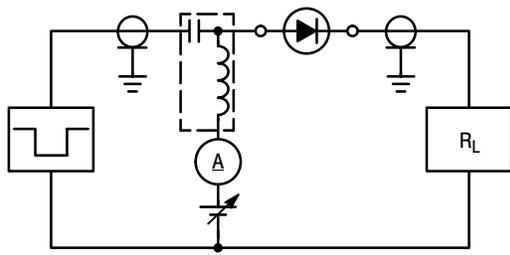
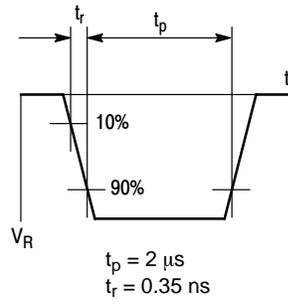


Figure 3. Diode Capacitance

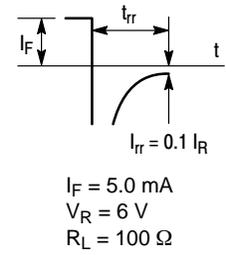
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RECOVERY TIME EQUIVALENT TEST CIRCUIT



INPUT PULSE



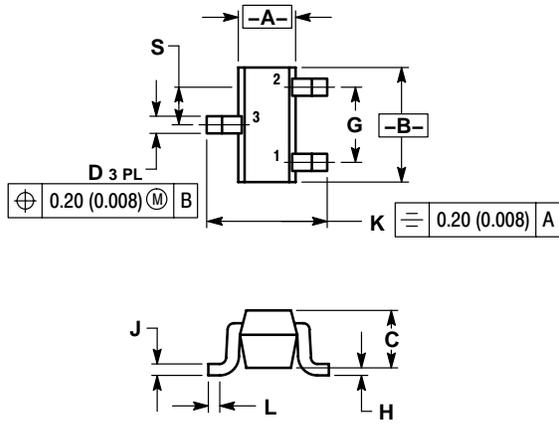
OUTPUT PULSE

Figure 4. Reverse Recovery Time Test Circuit for the DAN222

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PACKAGE DIMENSIONS

SOT-416/SC-90 CASE 463-01 ISSUE C



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.70	0.90	0.028	0.035
B	1.40	1.80	0.055	0.071
C	0.60	0.90	0.024	0.035
D	0.15	0.30	0.006	0.012
G	1.00 BSC		0.039 BSC	
H	---	0.10	---	0.004
J	0.10	0.25	0.004	0.010
K	1.45	1.75	0.057	0.069
L	0.10	0.20	0.004	0.008
S	0.50 BSC		0.020 BSC	

STYLE 3:

1. ANODE
2. ANODE
3. CATHODE

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